Schedule by Room 1

R	oom	Cap.	September	17 (Wed.)	September	· 18(Thu.)	Septembe	er 19 (Fri.)	Septembe	r 20 (Sat.)
Room		Cap.	AM	PM	AM	PM	AM	PM	AM	PM
-	A1 大講堂	450		12.5 Organic solar cells	12.5 Organic solar cells	Symposium: Micro and nano behavior of bio material surfaces and its application	cells	12.5 Organic solar cells		
	A2 N1	110	Tutorial	12.2 Characterization and Materials Physics	Materials Physics	12.2 Characterization and Materials Physics	12.7 Medical Engineering and Biochips	12.7 Medical Engineering and Biochips	12.7 Medical Engineering and Biochips	12.7 Medical Engineering and Biochips
	A3 N2	110	12.3 Functional materials and novel devices	12.3 Functional materials and novel devices	12.3 Functional materials and novel devices	12.3 Functional materials and novel devices	12.6 Nanobiotechnology	12.6 Nanobiotechnology	12.6 Nanobiotechnology	
	A4 E201	140	emitting devices and	12.4 Organic light- emitting devices and organic transistors	12.4 Organic light- emitting devices and organic transistors	12.4 Organic light- emitting devices and organic transistors	Symposium: Innovation in R&D of the Flexible Electronics -Toward the Inorganic Flexible Devices-	Innovation in R&D of the Flexible Electronics -Toward the Inorganic Flexible Devices-		12.4 Organic light- emitting devices and organic transistors
	A5 E204	70	12.1 Fabrications and Structure Controls	12.1 Fabrications and Structure Controls	12.1 Fabrications and Structure Controls			12.4 Organic light- emitting devices and organic transistors		
	A6 E205	70	and vacuum	6.5 Surface physics and vacuum	9.2 Nanowires, nanoparticles	9.2 Nanowires, nanoparticles	9.2 Nanowires, nanoparticles	9.5 New functional materials and new physical properties		
	A7 E206	70	12.7 Medical Engineering and Biochips		9.4 Thermoelectric conversion	9.4 Thermoelectric conversion	9.3 Nanoelectronics	9.3 Nanoelectronics		
	A8 E207	70	6.2 Carbon-based thin films	6.2 Carbon-based thin films	6.2 Carbon-based thin films	6.2 Carbon-based thin films	6.6 Probe microscopy	6.6 Probe microscopy		
	A9 E208	116	Tutorial	Tutorial	6.1/9.1 code- sharing session	6.1/9.1 code- sharing session	6.1/9.1 code- sharing session	6.1/9.1 code- sharing session		
	A10 E214	116	6.3 Oxide-based electronics	6.3 Oxide-based electronics	6.3 Oxide-based electronics	Symposium: Oxide electronics at solid- liquid interfaces: Chemistry and device applications	6.3 Oxide-based electronics	6.3 Oxide-based electronics	6.3 Oxide-based electronics	6.3 Oxide-based electronics
	A11 E215	70		6.4 New thin-film materials	6.4 New thin-film materials	6.4 New thin-film materials				
	A12 E301	140	Tutorial	14.5/15.2 code- sharing session	Joint Session K "Wide bandgap oxide semiconductor materials and devices"	Joint Session K "Wide bandgap oxide semiconductor materials and devices"	Joint Session K "Wide bandgap oxide semiconductor materials and devices"	Joint Session K "Wide bandgap oxide semiconductor materials and devices"	Joint Session K "Wide bandgap oxide semiconductor materials and devices"	
	A13 E304	70	interfaces by X-ray reflectivity and surface X-ray scattering - Towards	Symposium: Phase problem in the analysis of buried interfaces by X-ray reflectivity and surface X-ray scattering - Towards new research with coherent light sources	beam-induced surface reactions 7.8 New beam-	Symposium: Surface reaction control by atomic and molecular beams, its development and application		7.1 X-ray technologies	7.4 Nanoimprint	7.4 Nanoimprint
A	A14 E305	70	7.3 Lithography	Symposium: Interfacial nano electrochemistry: Research frontiers of semiconductor wet processes		7.6 Ion beams	7.2 Electron microscopes, evaluation, measurement and analysis	7.7 Vacuum nanoelectronics and electron sources		
	A15 E306	70			13.5 Si-English Session	1.8 Ultrasonic	13.1 Basic Properties, Surface and Interface Phenomena, and Simulation	13.1 Basic Properties, Surface and Interface Phenomena, and Simulation		
	A16 E307	70		13.4 Devices/ Integration Technologies	13.4 Devices/ Integration Technologies	13.4 Devices/ Integration Technologies	crystals and IV-IV-	15.5 IV-group crystals and IV-IV- group mixed crystals		
	A17 E308	116	15.6 IV-group-based compounds	15.6 IV-group-based compounds	15.6 IV-group-based compounds	15.6 IV-group-based compounds	13.2 Insulator technology	13.2 Insulator technology Symposium: New	15.1 Bulk crystal growth	15.1 Bulk crystal growth
	A18 E310	140			3.15 Silicon photonics	3.15 Silicon photonics	3.15 Silicon photonics	Frontiers and Future Perspectives in Surface Reaction Observation Using Synchrotron Radiation		
	A19 E311	116	Tutorial	Symposium: Low- Temperature Growth of Group-IV Semiconductors on Insulator - Emerging New Crystallization Techniques -	13.3 Si Process • Interconnect • MEMS • Integration	13.3 Si Process • Interconnect • MEMS • Integration	13.3 Si Process • Interconnect • MEMS • Integration	13.3 Si Process • Interconnect • MEMS • Integration	13.3 Si Process • Interconnect • MEMS • Integration	
	A20 E312	70	11.5 Junction, circuit fabrication process and digital applications	11.5 Junction, circuit fabrication process and digital applications	15.3 III-V-group epitaxial crystals	15.7 Fundamentals of epitaxy 15.3 III-V-group epitaxial crystals	11.2 Thin films, thick films, coated conductors and thin film crystal growth	11.2 Thin films, thick films, coated conductors and thin film crystal growth	15.8 Crystal evaluation, impurities and crystal defects	
	A21 E313	70		11.3 Critical current, superconducting power applications		11.1 Fundamental properties	11.1 Fundamental properties	11.1 Fundamental properties		
	A22 E314	70			14.3 Electron devices and Process technology	14.3 Electron devices and Process technology	11.4 Analog application and its related technologies	11.4 Analog application and its related technologies	11.4 Analog application and its related technologies	
-	A23 E315	70	1.1 Interdisciplinary and General Physics	1.3 Novel Technologies and Frontier Engineering Science		Symposium: Activity of the scientific enlightenment including upbringing of the student	1.4 Energy conversion and storage	Resource Recycling and Energy Utilization from View Point of Applied Physics		
	A24 E317	70			14.4 Optical properties and light- emitting devices	1.6 Magnetic field and its application	1.5 Resources and environment	1.7 Instrumentation and measurement, metrology		
	A25 E318	70		Symposium: Current situation and issues of thin- film silicon solar cell technologies	16.3 Bulk, thin-film and other silicon- based solar cells	16.3 Bulk, thin-film and other silicon- based solar cells	16.3 Bulk, thin-film and other silicon- based solar cells	16.3 Bulk, thin-film and other silicon- based solar cells	16.3 Bulk, thin-film and other silicon- based solar cells 16.2 Processing technologies and devices	

Schedule by Room 2

Room		Cap.	September 17 (Wed.)		September 18 (Thu.)		September 19 (Fri.)		September 20 (Sat.)	
			AM	PM	AM	PM	AM	PM	AM	PM
	A26 E319	70			16.1 Fundamental properties and their evaluation in disordered materials	16.1 Fundamental properties and their evaluation in disordered materials	14.4 Optical properties and light- emitting devices	14.4 Optical properties and light- emitting devices	14.4 Optical properties and light- emitting devices	14.4 Optical properties and light- emitting devices
Α	A27 N302	90	19.4 14.3/15.4 code-sharing session	19.4 14.3/15.4 code-sharing session	14.2 Ultrathin films and quantum nanostructures	14.2 Ultrathin films and quantum nanostructures	14.2 Ultrathin films and quantum nanostructures	14.1 Physical properties of exploratory materials	14.1 Physical properties of exploratory materials	
	A28 N304	90		14.5 Compound solar cells	14.5 Compound solar cells	14.5 Compound solar cells	14.5 Compound solar cells			
	S1 S1	250	Japan-Korea Joint Symposium on Semiconductor Physics and Technology - Nano- carbon materials including graphene -	Japan-Korea Joint Symposium on Semiconductor Physics and Technology - Nano- carbon materials including graphene -	8. Plasma Electronics: Award Speech	Symposium: Computer Simulations for Plasma Processing (state-of-the-art plasma modelling)	14.5/15.3/15.4 code-sharing session			
S	S2 52	346	10.1 Creation of new materials	10.1 Creation of new materials (Short oral presentation) 10.2 Spin torque, spin current, circuits, and measurement technologies (Short oral presentation) 10.3 Giant magnetoresistance (GMR), tunnel magnetoresistance (TMR) and magnetic recording technologies (Short oral presentation) 10.4 Semiconductors, organic, optical, and quantum spintronics (Short oral presentation)	10.1 Creation of new materials	Symposium: Frontier of Spintronic Materials and Devices	10.3 Giant magnetoresistance (GMR), tunnel magnetoresistance (TMR) and magnetic recording technologies	10.4 Semiconductors, organic, optical, and quantum spintronics	10.2 Spin torque, spin current, circuits, and measurement technologies	10.2 Spin torque, spin current, circuits, and measurement technologies
	S8 S8	70	3.8 Optical measurement technology and devices	3.8 Optical measurement technology and devices	3.8 Optical measurement technology and devices	3.8 Optical measurement technology and devices	8.1 Plasma production and control	8.1 Plasma production and control 8.6 General plasma phenomena, emerging area of plasmas and their new applications	8.6 General plasma phenomena, emerging area of plasmas and their new applications	8.6 General plasma phenomena, emerging area of plasmas and their new applications
	S9 S9	70	3.7 Laser processing	3.7 Laser processing	3.7 Laser processing	3.7 Laser processing	8.3 Plasma deposition of thin film and surface treatment	8.3 Plasma deposition of thin film and surface treatment	8.5 Plasma nanotechnology	8.5 Plasma nanotechnology
	S10 S10	70	8. Plasma	8. Plasma Electronics: Invited Lecture of Overseas Researcher 8. Plasma Electronics: English Session				8.4 Plasma etching	10.4 Semiconductors, organic, optical, and quantum spintronics	
	S11	70		8.2 Plasma measurements and diagnostics			3.3 Information photonics and image engineering	3.3 Information photonics and image engineering		
	B1 セミナー1	105	17.4 Device application	17.4 Device application 17.2 Structural control and process		17.3 Exploration of new functions and evaluation of basic properties	17.4 Device application	17.2 Structural control and process 17.3 Exploration of new functions and evaluation of basic properties	17.1 Growth technology	
В	B2 セミナー2	87		2.1 Radiation physics and detectors	2.3 Application of radiation, radiation generators and technologies	2.2 Detection systems	2.2 Detection systems	Symposium: Behavior of nuclear fuel and fission products during severe accident and activities on decontamination	2.2 Detection systems	2.2 Detection systems
	B3 ホール	256	Special Events (See p. ENG-14)	Special Events (See p. ENG-14)	JSAP President Special Lecture	Symposium: Present and Future of Functional atomic thin film research	17.1 Growth technology	17.1 Growth technology	17.1 Growth technology	
С	C1 B11	78	3.12 Nanoscale optical science and near-field optics	3.12 Nanoscale optical science and near-field optics	3.12 Nanoscale optical science and near-field optics	3.12 Nanoscale optical science and near-field optics	3.1 Basic optics and frontier of optics	3.1 Basic optics and frontier of optics	18.5 Opto- electronics	18.5 Opto- electronics
	C2 B12	72			3.10 Optical quantum physics and technologies	3.10 Optical quantum physics and technologies	3.6 Ultrashort-pulse and high-intensity lasers	3.6 Ultrashort-pulse and high-intensity lasers	3.6 Ultrashort-pulse and high-intensity lasers	
	C3 B31	84	18.8 Carbon Photonics	18.8 Carbon Photonics	18.4 Optical Micro-sensing, Manipulation, and Fabrications	18.4 Optical Micro-sensing, Manipulation, and Fabrications	18.1 Plasmonics	18.1 Plasmonics	18.1 Plasmonics	
	C4 B32	84	18.7 Laser Photonics-XFEL and ultrafast optics-	OSA President Special Lecture 18.7 Laser Photonics-XFEL and ultrafast optics-	18.2 Bio- and Medical Photonics	18.2 Bio- and Medical Photonics	18.2 Bio- and Medical Photonics	18.3 Laser Manufacturing	18.6 Information Photonics	18.6 Information Photonics
	C5 オープンホール	364	15.4 III-V-group nitride crystals	15.4 III-V-group nitride crystals	15.4 III-V-group nitride crystals	15.4 III-V-group nitride crystals	Singularity in Nitride semiconductors \sim	Symposium: Materials Science of Singularity in Nitride semiconductors ~ Characterization and Crystallography ~	nitride crystals	15.4 III-V-group nitride crystals
	C6 C212	104	3.13 Semiconductor optical devices	3.13 Semiconductor optical devices	3.13 Semiconductor optical devices	3.13 Semiconductor optical devices	3.9 THz technology	3.9 THz technology	3.9 THz technology	3.9 THz technology
	C7 C213	104	3.2 Materials and equipment optics	3.2 Materials and equipment optics	3.14 Optical control devices and optical fiber	3.14 Optical control devices and optical fiber	3.14 Optical control devices and optical fiber	Symposium: Frontiers in Quantum Metrology	3.4 Biomedical optics	3.4 Biomedical optics
	C8 C310	72		3.11 Photonic structures and phenomena	3.11 Photonic structures and phenomena	3.11 Photonic structures and phenomena	3.5/3.14 code- sharing session	3.5 Laser devices and materials	3.5 Laser devices and materials	3.5 Laser devices and materials

Schedule by Room 3

Room		Cap.	September 17 (Wed.)		September 18 (Thu.)		September 19 (Fri.)		September	20 (Sat.)
			AM	PM	AM	PM	AM	PM	AM	PM
PA(第1体育館)	PA1 5 PA12		12.2 Characterization and Materials Physics 12.5 Organic solar cells 13.4 Devices/ Integration Technologies	[1:30 pm - 3:30 pm] 13.3 Si Process • Interconnect • MEMS • Integration	12.6 Nanobiotechnology 12.7 Medical Engineering and Biochips 17. Nanocarbon Technology	 [1:30 pm - 3:30 pm] 3.2 Materials and equipment optics 3.3 Information photonics and image engineering 3.5 Laser devices and materials 3.6 Ultrashort-pulse and high-intensity lasers 3.9 Tlz technology 	1.3 Novel Technologies and Frontier Engineering Science 1.7 Instrumentation and measurement, metrology 1.8 Ultrasonic 3.4 Biomedical	11:30 pm - 3:30 pm] 3.14 Optical control devices and optical fiber 7.5 Particle/photon- beam-induced surface reactions 7.6 Ion beams	3.1 Basic optics and frontier of optics 13.1 Basic Properties, Surface and Interface Phenomena, and Simulation 13.2 Insulator technology	
				[4:00 pm - 6:00 pm] 3.11 Photonic structures and phenomena 3.15 Silicon photonics 6.1/9.1 code- sharing session K "Wide bandgap oxide semiconductor materials and devices"		[4:00 pm - 6:00 pm] 2. Ionizing Radiation 6:3 Oxide-based electronics 6.6 Probe microscopy	optics 3.7 Laser processing 3.8 Optical measurement technology and devices 3.10 Optical quantum physics and technologies 3.13 Semiconductor optical devices	4:00 pm - 6:00 pm] 9.2 Nanowires, nanoparticles 9.4 Thermoelectric conversion 12.3 Functional materials and novel devices 12.4 Organic light- emitting devices and organic transistors		
PB(第2体育館)	РВ1 5 РВ12	Poster Session	8.1 Plasma production and control	[1:30 pm - 3:30 pm] 9.3 Nanoelectronics 9.5 New functional materials and new physical properties	1.1 Interdisciplinary and General Physics 1.2 Education 1.3 Novel Technologies and Frontier Engineering Science 1.4 Energy conversion and storage 1.5 Resources and environment 11. Superconductivity	14.4 Optical properties and light- emitting devices 15.1 Bulk crystal growth 15.5 IV-group crystals and IV-IV- group mixed crystals	6.2 Carbon-based thin films 6.4 New thin-film materials 6.5 Surface physics and vacuum 14.1 Physical properties of exploratory materials 15.6 IV-group-based compounds	[4:00 pm - 6:00 pm] 15.2 II-VI-group crystals and multicomponent		
			10. Spin	[4:00 pm - 6:00 pm] 10. Spintronics and Magnetics		3.12 Nanoscale optical science and near-field optics 12.1 Fabrications and Structure Controls		multicomponent crystals 15.3 III-V-group epitaxial crystals 15.4 III-V-group nitride crystals 15.8 Crystal evaluation, impurities and crystal defects		